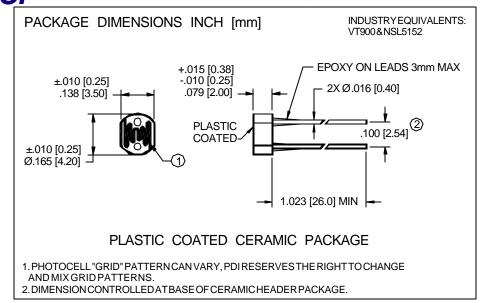
PHOTONIC Cadmium Sulfoselenide (CdS) Photoconductive Photocells

Type PDV-P9XXX-X





### **FEATURES**

- Visible light response
- Sintered construction
- Low cost
- High Reliability

#### DESCRIPTION

PDV-P9XXX-X are (CdS) photoconductive photocells designed to sense light from 400 nm to 700 nm. As light dependent resistors, they are available in a wide range of resistance values. They are packaged in a two leaded plastic-coated ceramic header.

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

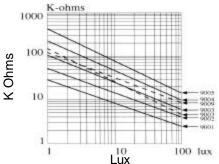
SYMBOL	PARAMETER	MIN	MAX	UNITS
VPK	Applied Voltage		150	V dc
P <sub>da poát</sub>	Continuous Power Dissipation		90	mW/ºC
T <sub>stg</sub> & T <sub>o</sub>	OperatingTemperatureRange&Storage	-30	+75	∘C
Ts	Soldering Temperature*		+260	∘C

 $<sup>^*.200\,</sup>inch\,(5\,mm)\,from\,bottom\,of\,header\,for\,3\,secs\,max\,with\,heat\,sink$ 

## **APPLICATIONS**

- Cameraexposure
- Low light level
- Shutter controls
- Night light controls

#### **CELL RESISTANCE VS. ILLUMINANCE**



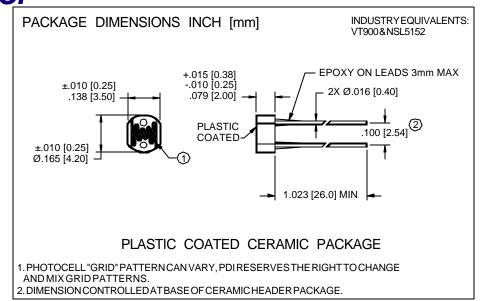
### ELECTRO-OPTICAL CHARACTERISTICS TA=25°C (2 HOURS LIGHT ADAPT, MIN)\*\*\*

MODEL NO.	CELL RESISTANCE** (Ohms)				SENSITIVITY	SPECTRALPEAK	RESPONSETIME @10 Lux	
	10 Lux @	2856K	DARK	(	LOG(R100)-LOG(R10) LOG (E100)-LOG(E10) (\(\lambda\) TYP)	(nm)	RISE TIME (ms)	FALL TIME (ms)
N	IN(KΩ) I	IAX (KΩ)	MIN (M $\Omega$ )	SEC		TYP	TYP	TYP
PDV-P9001	4	11	0.3	10	0.65	520	60	25
PDV-P9002	9	20	0.5	10	0.6	520	60	25
PDV-P9002-1	11	20	0.5	10	0.7	520	60	25
PDV-P9003	16	33	1	10	0.8	520	60	25
PDV-P9003-1	23	33	1	10	0.85	520	60	25
PDV-P9004	27	60	2	10	0.85	520	60	25
PDV-P9005	50	94	2.5	10	0.9	520	60	25
PDV-P9005-1	48	140	20	10	0.9	520	60	25

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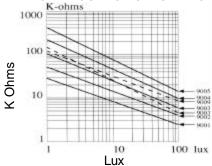
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VPK	Applied Voltage		150	V dc
P <sub>d<b>∆</b> po<b>∆</b>t</sub>	Continuous Power Dissipation		90	mW/ºC
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 $<sup>\</sup>star$ .200 inch (5 mm) from bottom of header for 3 secs max with heat sink

### **APPLICATIONS**

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CELL RESISTANCE VS. ILLUMINANCE



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	10 Lux @2856K		DARK		LOG(R100)-LOG(R10)	(nm)	RISE TIME (ms)	FALL TIME (ms)
ľ	VIIN (K $\Omega$ )	$MAX\left(K\Omega\right)$	$MIN(M\Omega)$	SEC	LOG (E100)-LOG(E10) (	TYP	TYP	TYP
PDV-P9006	80	200	5	10	1	520	60	25
PDV-P9007	10	100	1	10	0.8	520	60	25
PDV-P9008	10	200	20	10	0.85	520	60	25
PDV-P9103	20	45	1	10	0.8	520	60	25
PDV-P9200	10	50	5	10	0.9	520	70	15
PDV-P9203	5	20	20	10	0.9	520	70	15